

- GENERAL PURPOSE SILICON DIODES
- ALL JUNCTIONS COMPLETELY PROTECTED WITH SILICON DIOXIDE
- COMPATIBLE WITH ALL WIRE BONDING AND DIE ATTACH TECHNIQUES EXCEPT SOLDER REFLOW

CD483B
 CD485B
 CD486B
 CD645
 AND
 CD5194 thru CD5196

MAXIMUM RATINGS

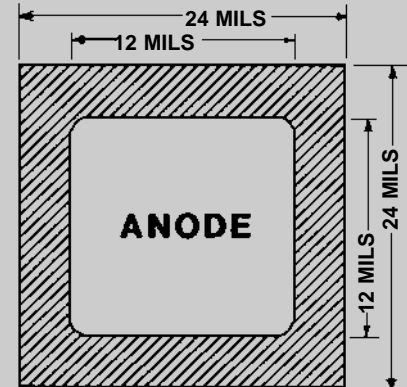
Operating Temperature: -65°C to +175°C
 Storage Temperature: -65°C to +175°C

ELECTRICAL CHARACTERISTICS @ 25°C, unless otherwise specified

TYPE	V_{RM}	V_{RWM}	I_O	I_O	I_{FSM}
	$V_{(pk)}$	$V_{(pk)}$	mA	$T_A=+150^\circ C$ mA	$t_p = 1/120 S$ $T_A=25^\circ C$ A
CD483B	80	70	200	50	2
CD485B	180	180	200	50	2
CD486B	250	225	200	50	2
CD645	270	225	400	150	5
CD5194	80	70	200	50	2
CD5195	180	180	200	50	2
CD5196	250	225	200	50	2

TYPE	$V_F(1)$	I_{R1} at V_{RWM}	I_{R2} at V_{RM}	I_{R3} at V_{RWM}	CAP
	V dc	nA dc	$T_A=25^\circ C$ μA	$T_A=150^\circ C$ μA dc	@ V_R =4V pF
CD483B	0.8 - 1.0	25	100	5	-
CD485B	0.8 - 1.0	25	100	5	-
CD486B	0.8 - 1.0	25	100	5	-
CD645	0.8 - 1.0	50	50	25	2.0
CD5194	0.8 - 1.0	25	100	5	-
CD5195	0.8 - 1.0	25	100	5	-
CD5196	0.8 - 1.0	25	100	5	-

NOTE 1 AT 100mA (pulsed) except for CD645 which is at 400mA (pulsed)



DESIGN DATA

METALLIZATION:

Top: (Anode).....Al
 Back: (Cathode).....Au

AL THICKNESS25,000 Å Min

GOLD THICKNESS4,000 Å Min

CHIP THICKNESS10 Mils

TOLERANCES: ALL
 Dimensions \pm 2 mils



CD483B, CD485B, CD486B, CD645, CD5194 thru CD5196

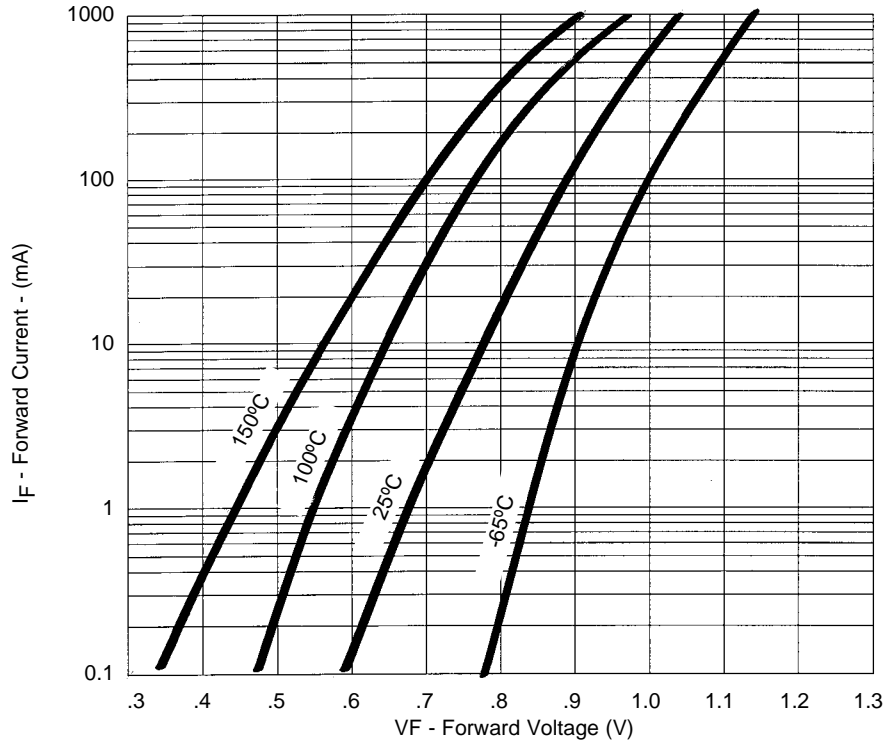
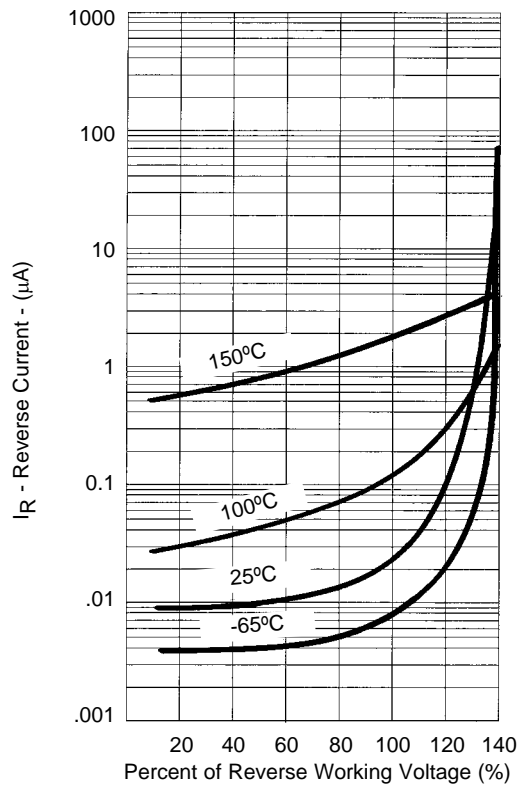


FIGURE 2
Typical Forward Current
vs Forward Voltage



NOTE : All temperatures shown on graphs are junction temperatures

FIGURE 3
Typical Reverse Current
vs Reverse Voltage